



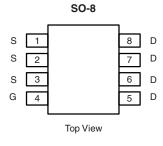
P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 30	0.030 at V _{GS} = - 10 V	- 7.5		
	0.050 at V _{GS} = - 4.5 V	- 5.8		

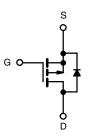
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs





Ordering Information: Si4431BDY-T1-E3 (Lead (Pb)-free) Si4431BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_{μ}	$_{\chi}$ = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current /T = 150 °C\a	T _A = 25 °C	I_	- 7.5		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	- 'D	- 6.0	- 4.6	^
Pulsed Drain Current		I _{DM}	- 30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.1	- 1.2	
Martine Daniel Distriction	T _A = 25 °C	P _D	2.5	1.5	W
Maximum Power Dissipation ^a	T _A = 70 °C	1 ' ^D	1.6	0.9	v V
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R_{thJA}	38	50	
Maximum Junction-to-Ambient	Steady State	itnJA	70 85	85	°C/W
Maximum Junction-to-Foot	Steady State	R _{thJF}	22	28	

a. Surface Mounted on 1" x 1" FR4 board.

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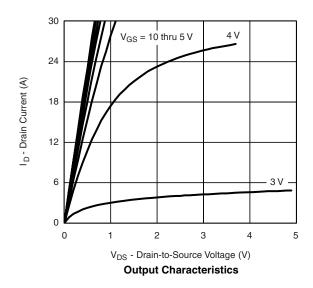
SPECIFICATIONS $T_J = 25$,		
Parameter	Symbol	Test Conditions Mi		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zara Cata Valtaga Drain Current		V _{DS} = - 30 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = - 30 V, V_{GS} = 0 V, T_{J} = 70 °C			- 10	μΑ	
0.01.0.13	1	V _{DS} = - 5 V, V _{GS} = - 10 V	- 30				
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 7			Α	
	Ь	V _{GS} = - 10 V, I _D = - 7.5 A		0.023 0.0	0.030		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -5.8 \text{ A}$		0.036	0.050	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 7.5 A		18		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 2.1 A, V _{GS} = 0 V		- 0.78	- 1.1	V	
Dynamic ^b							
Total Gate Charge	Q_g			13	20		
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -5 \text{ V}, I_{D} = -7.5 \text{ A}$		3.6		nC	
Gate-Drain Charge	Q_{gd}			6			
Turn-On Delay Time	t _{d(on)}			10	20		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		10	20		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, V_{GEN} = - 10 V, R_G = 6 Ω		70	110	ns	
Fall Time	t _f			47	70		
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = -2.1 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$		45	80		

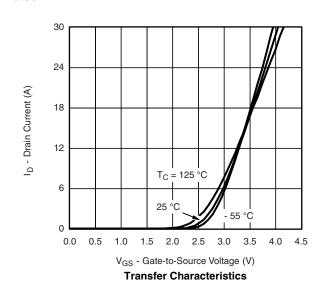
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

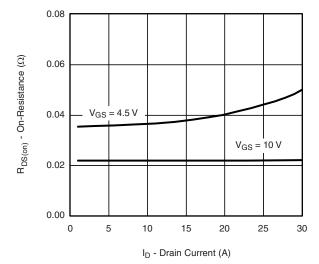




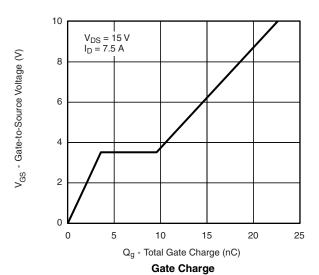


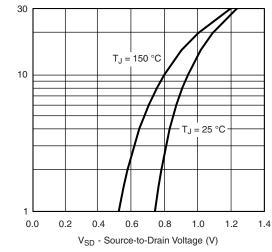


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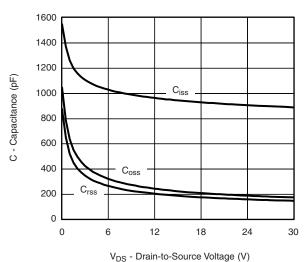


On-Resistance vs. Drain Current

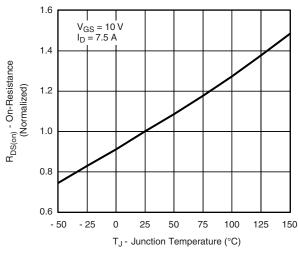




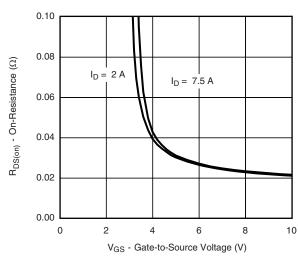
Source-Drain Diode Forward Voltage



Capacitance



On-Resistance vs. Junction Temperature



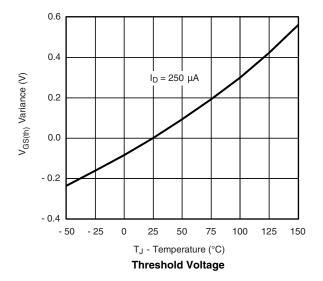
On-Resistance vs. Gate-to-Source Voltage

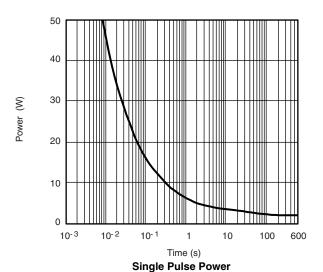
Is - Source Current (A)

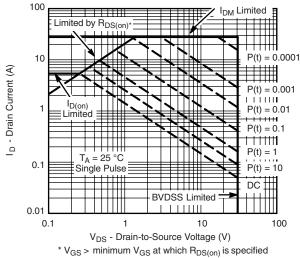
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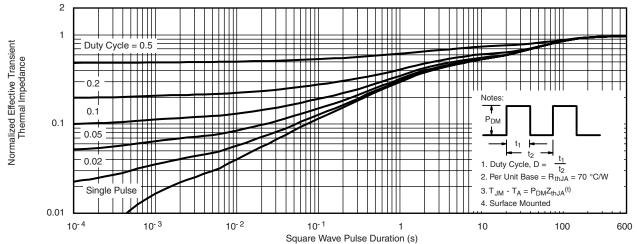
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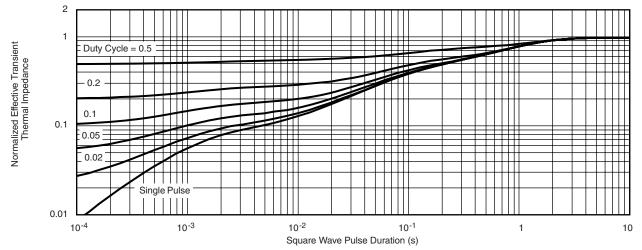
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



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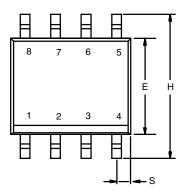


Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72092.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
FCN: C-06527-Bey 11-Sen-06					

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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